The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-27 (Canceled)

28. (Previously Presented) A method for processing a semiconductor substrate, said method comprising:

continuously delivering plasma forming components to a process chamber;

via time multiplexing, selectively switching the delivery of the plasma forming components back and forth between a first delivery condition where the plasma forming components are only delivered to an inner region of the process chamber, and a second delivery condition where the plasma forming components are only delivered to an outer region of the process chamber so as to effect the concentration of the plasma forming component in an inner and an outer region of the process chamber, the first delivery condition allowing the plasma forming components to be delivered into an inner region of a process chamber while at the same time preventing the same plasma forming components from being delivered into an outer region of the process chamber, the second delivery condition allowing the plasma forming components to be delivered into the outer region of the process chamber while at the same time preventing the same plasma forming components from being delivered into the inner region of the process chamber;

continuously delivering second plasma forming components to the process chamber;

via a second time multiplexing operation that is separate from the time multiplexing operation associated with the plasma forming components, selectively switching the delivery of the second plasma forming components back and forth between a first delivery condition where the second plasma forming components are only delivered to an inner region of the process chamber, and a second delivery condition where the second plasma forming components are only delivered to an outer region of the process chamber so as to effect the concentration of the second plasma forming component in an inner and an outer region of the process chamber, the first delivery condition allowing the second plasma forming components to be delivered into an inner region of a process chamber while at the same time preventing the same second plasma forming components from being delivered into an outer region of the process chamber, the second delivery condition allowing the second plasma forming components to be delivered into the outer region of the process chamber while at the same

time preventing the same second plasma forming components from being delivered into the inner region of the process chamber,

wherein the plasma forming components correspond to energy, and the second plasma forming components correspond to gas.

Claim 29 (Canceled)

30. (Previously Presented) A method of forming a plasma associated with etching a semiconductor substrate, said method comprising:

continuously supplying power from a single power source;

continuously supplying a flow of gas from a single gas source while the power is being supplied;

via time multiplexing, alternately producing first and second electric fields inside the process chamber with the supplied power, the first electric field being produced at a first region of a processing zone, the second electric field being produced at a second region of the processing zone, the first and second electric fields being produced according to a power time sequence that is divided into a plurality of time slices;

controlling the parameters associated with the first and second electric fields at each time slice in order to effect the amount of ions in the first and second regions of the processing zone;

via time multiplexing, alternately releasing the supplied gas into the process chamber at a first region and a second region of the processing zone, the gases being released according to a gas time sequence that is divided into a plurality of time slices;

controlling the parameters associated with the released gas at each time slice in order to effect the amount of neutrals in the first and second regions of the processing zone.

31. (Previously Presented) The method as recited in claim 30 wherein the gas time sequence and power time sequence follow the same time scale.

32. (Previously Presented) The method as recited in claim 30 wherein the gas time sequence and power time sequence follow different time scales.

33. (Previously Presented) The method as recited in claim 30 wherein the amount of power used to create the first and second electric fields is different or wherein the time slices

used to create the first and second electric fields are different in order to effect the amount of ions in the first and second regions of the processing zone.

34. (Previously Presented) The method as recited in claim 30 wherein the flow rates delivered to the first region and the second region are different or wherein the time slices associated with releasing gas to the first region are different than the time slices associated with releasing gas to the second region in order to effect the amount of neutrals in the first and second regions of the processing zone.

35. (Currently Amended) The method as recited in claim ~~30~~ 38 wherein the parameters associated with the first and second electric fields are controlled so that the amount of ions in the outer region are different than the amount of ions in the inner region in order to improve processing uniformity.

36. (Currently Amended) The method as recited in claim ~~30~~ 38 wherein the parameters associated with the released gas are controlled so that the amount of neutrals in the outer region are different than the amount of neutrals in the inner region in order to improve processing uniformity.

37. (Previously Presented) The method as recited in claim 30 wherein the electric fields are inductively coupled into the process chamber.

38. (Previously Presented) The method as recited in claim 30 wherein the first and second regions correspond to an inner region and an outer region, and wherein the inner region is associated with a center portion of the substrate and the outer region is associated with an edge portion of the substrate.